

UN4121/4122/4123/4124/412X/412Y

Silicon PNP epitaxial planer transistor

For digital circuits

■ Features

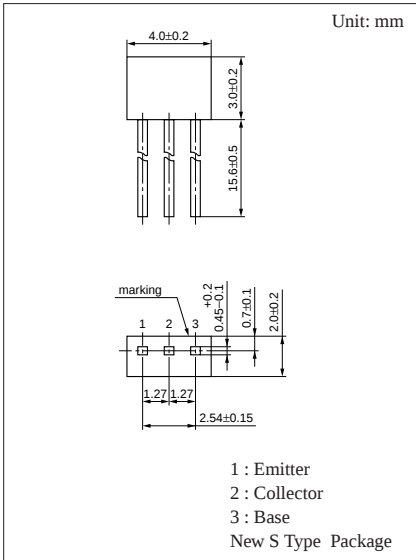
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.
- New S type package, allowing supply with the radial taping.

■ Resistance by Part Number

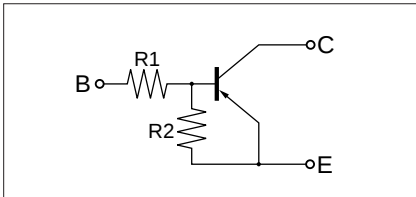
	(R ₁)	(R ₂)
• UN4121	2.2kΩ	2.2kΩ
• UN4122	4.7kΩ	4.7kΩ
• UN4123	10kΩ	10kΩ
• UN4124	2.2kΩ	10kΩ
• UN412X	0.27kΩ	5.0kΩ
• UN412Y	3.1kΩ	4.6kΩ

■ Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	-50	V
Collector to emitter voltage	V _{CEO}	-50	V
Collector current	I _C	-500	mA
Total power dissipation	P _T	300	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C



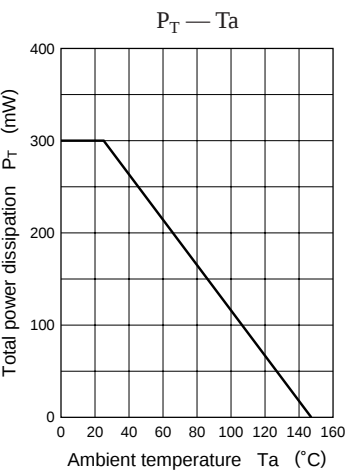
Internal Connection



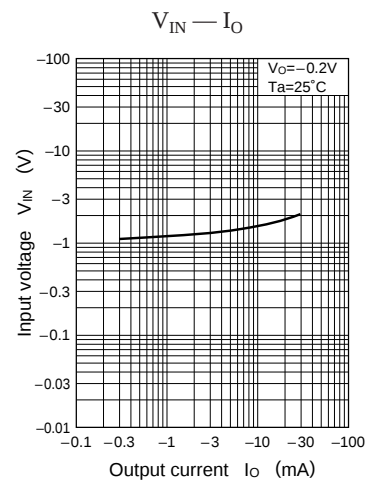
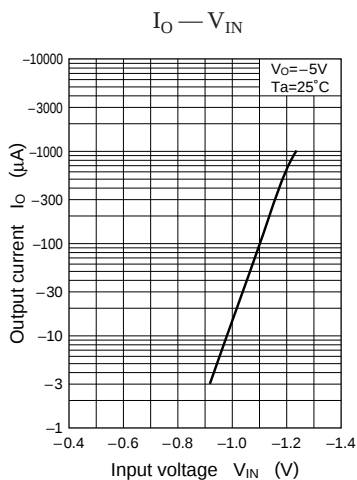
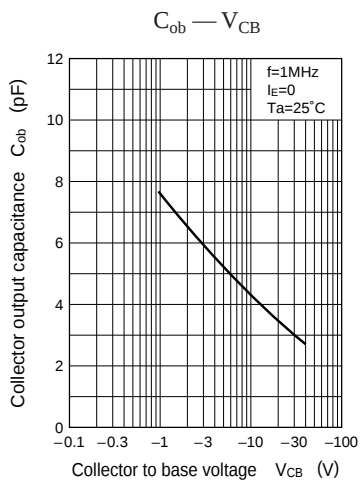
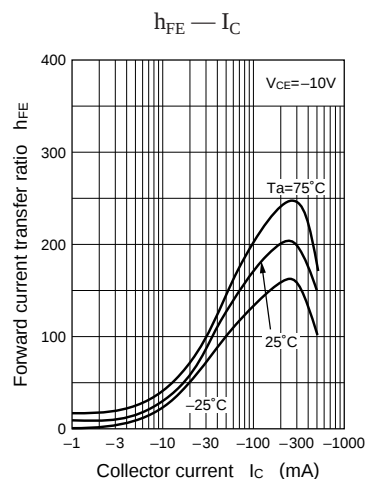
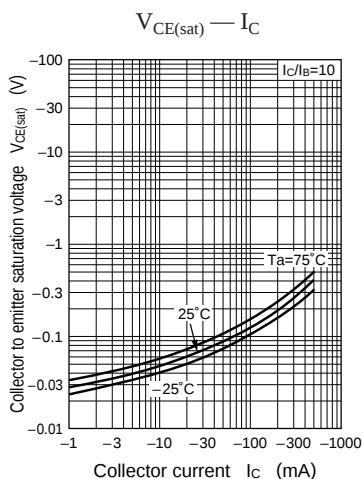
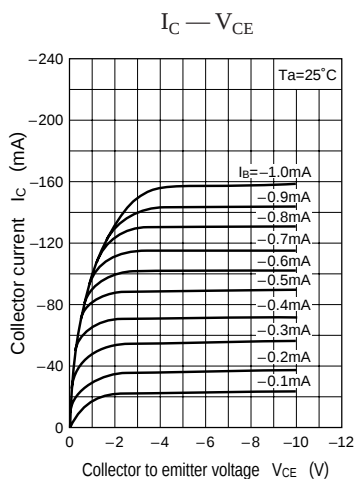
■ Electrical Characteristics (Ta=25°C)

Parameter		Symbol	Conditions	min	typ	max	Unit	
Collector cutoff current		I _{CBO}	V _{CB} = −50V, I _E = 0			−1	μA	
		UN412X I _{CBO}	V _{CB} = −50V, I _E = 0			−0.1		
Collector cutoff current		I _{CEO}	V _{CE} = −50V, I _B = 0			−1	μA	
		UN412X I _{CEO}	V _{CE} = −50V, I _B = 0			−0.5		
Emitter cutoff current	UN4121	I _{EBO}	V _{EB} = −6V, I _C = 0			−5	mA	
	UN4122/412X/412Y					−2		
	UN4123/4124					−1		
Collector to base voltage		V _{CBO}	I _C = −10μA, I _E = 0	−50			V	
Collector to emitter voltage		V _{CEO}	I _C = −2mA, I _B = 0	−50			V	
Forward current transfer ratio	UN4121	h _{FE}	V _{CE} = −10V, I _C = −100mA	40				
	UN4122/412Y			50				
	UN4123/4124			60				
	UN412X			20				
Collector to emitter saturation voltage		V _{CE(sat)}	I _C = −100mA, I _B = −5mA			−0.25	V	
		UN412X V _{CE(sat)}	I _C = −10mA, I _B = −0.3mA			−0.25		
		UN412Y V _{CE(sat)}	I _C = −50mA, I _B = −5mA			−0.15		
Output voltage high level		V _{OH}	V _{CC} = −5V, V _B = −0.5V, R _L = 500Ω	−4.9			V	
Output voltage low level		V _{OL}	V _{CC} = −5V, V _B = −3.5V, R _L = 500Ω			−0.2	V	
Transition frequency		f _T	V _{CB} = −10V, I _E = 50mA, f = 200MHz		80		MHz	
Input resistance	UN4121/4124	R ₁		(−30%)	2.2	(+30%)	kΩ	
	UN4122				4.7			
	UN4123				10			
	UN412X				0.27			
	UN412Y				3.1			
Resistance ratio		R ₁ /R ₂		0.8	1.0	1.2		
				UN4124	0.17	0.22		0.27
				UN412X	0.043	0.054		0.065
				UN412Y		0.67		

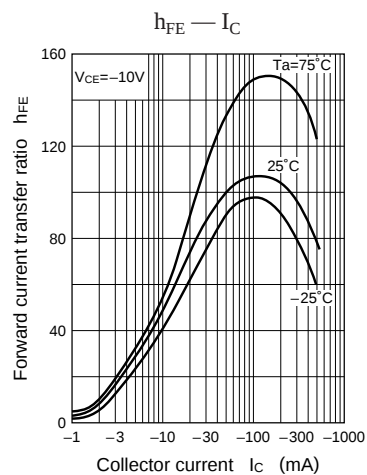
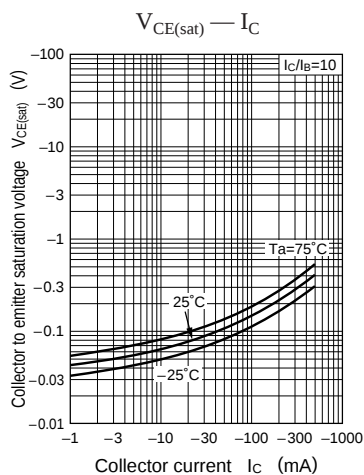
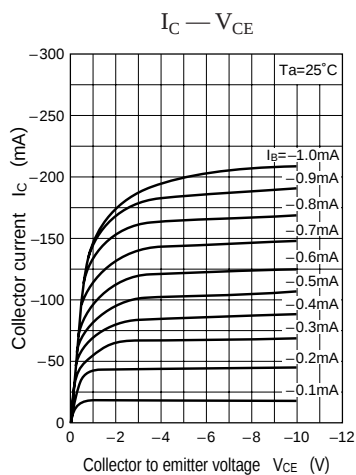
Common characteristics chart

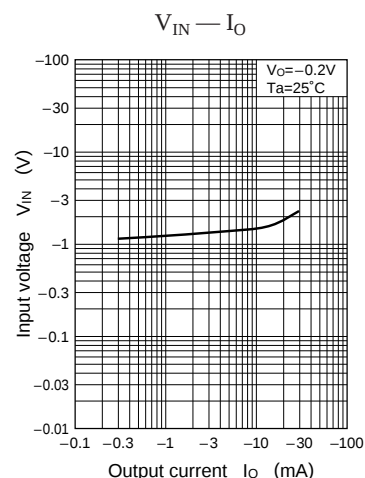
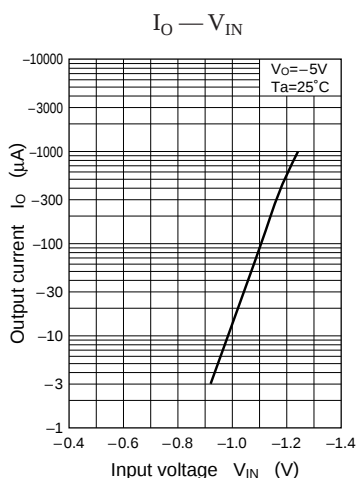
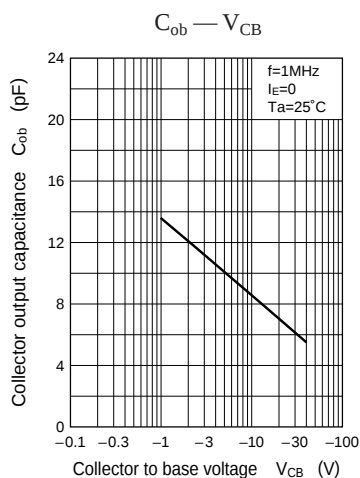


Characteristics charts of UN4121

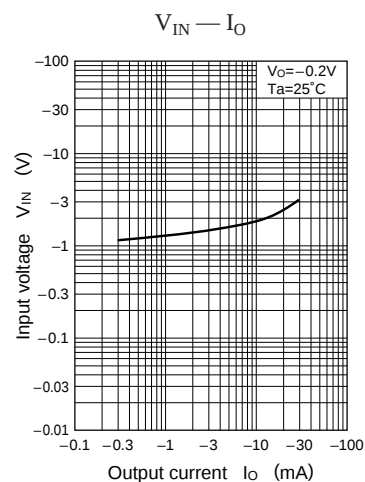
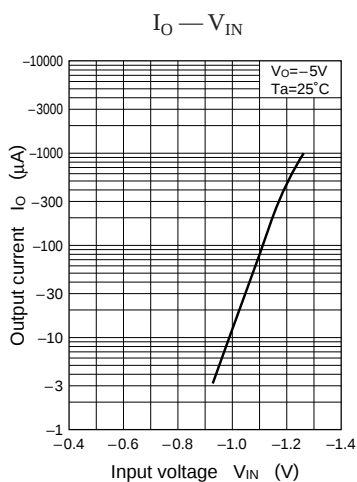
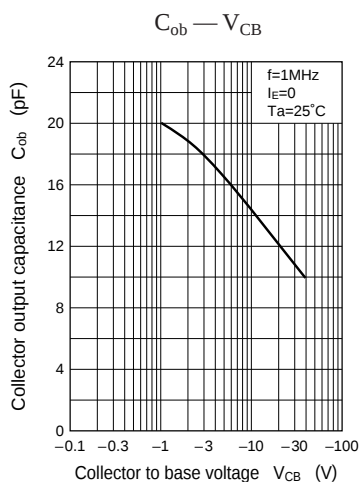
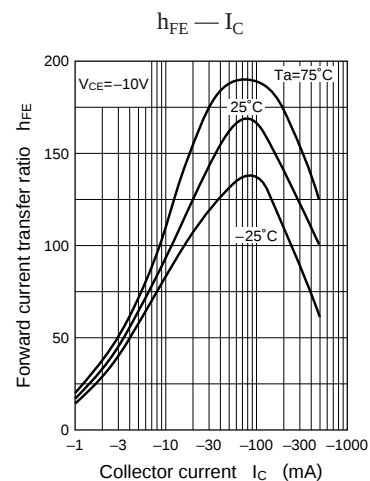
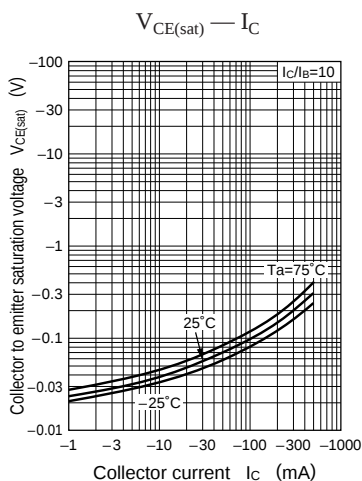
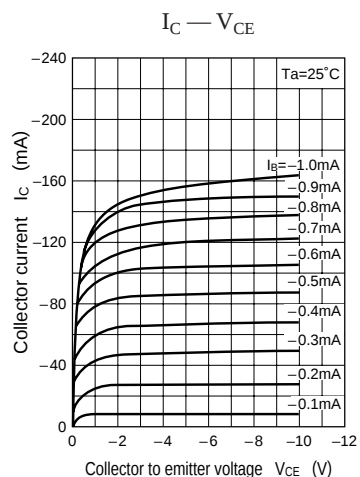


Characteristics charts of UN4122

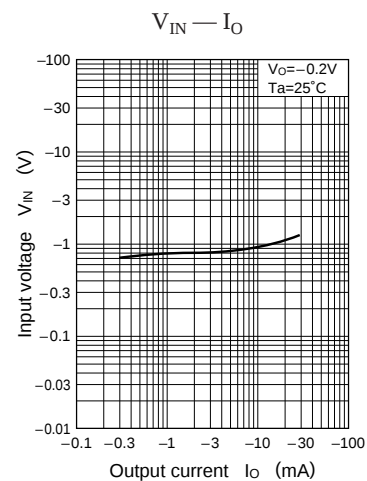
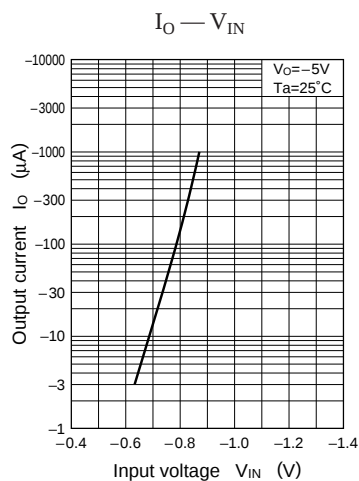
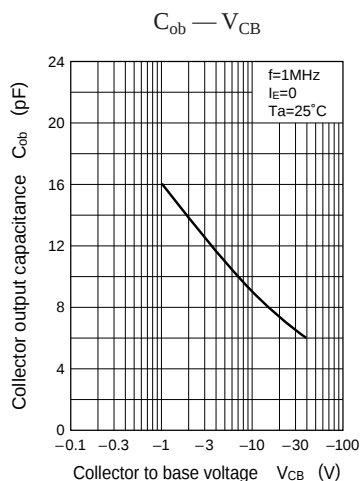
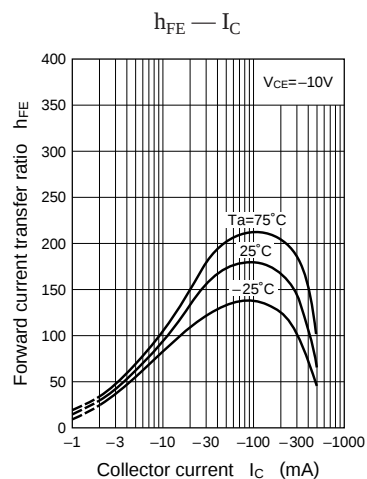
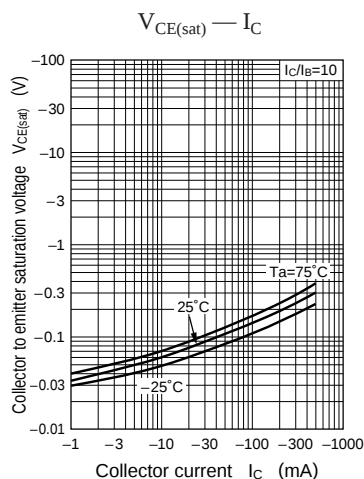
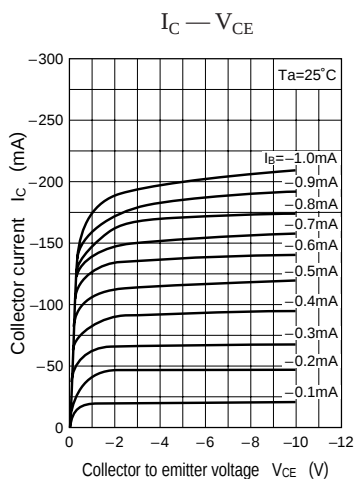




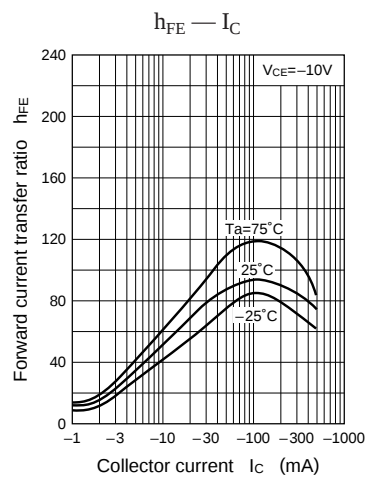
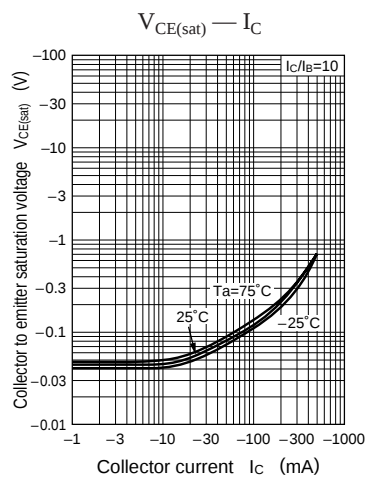
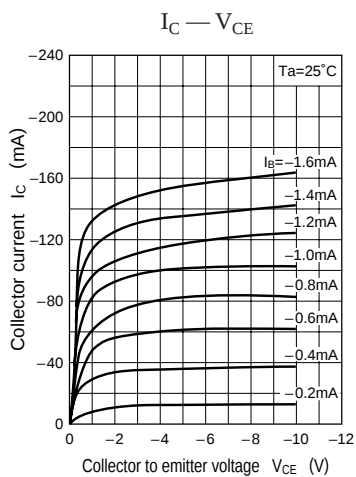
Characteristics charts of UN4123

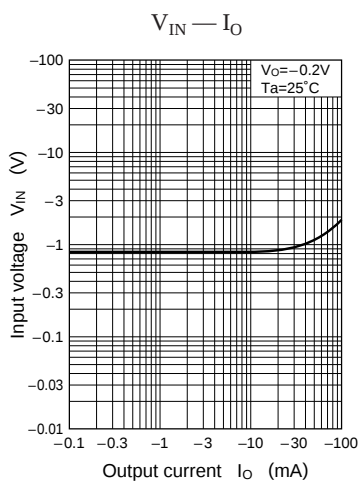
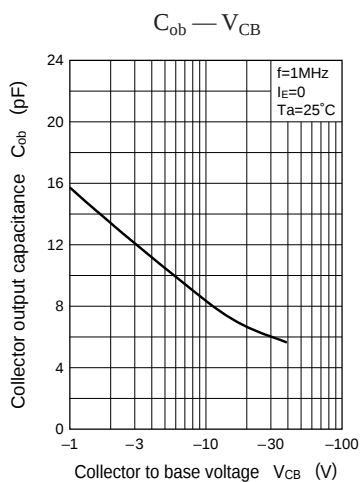


Characteristics charts of UN4124



Characteristics charts of UN412X





Characteristics charts of UN412Y

